# Octal 3-State Noninverting Transparent Latch with LSTTL Compatible Inputs

## **High-Performance Silicon-Gate CMOS**

The MC74HCT573A is identical in pinout to the LS573. This device may be used as a level converter for interfacing TTL or NMOS outputs to High–Speed CMOS inputs.

These latches appear transparent to data (i.e., the outputs change asynchronously) when Latch Enable is high. When Latch Enable goes low, data meeting the setup and hold times becomes latched.

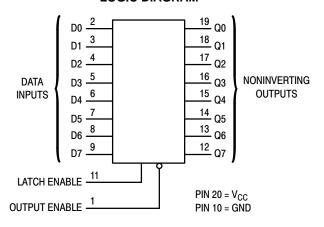
The Output Enable input does not affect the state of the latches, but when Output Enable is high, all device outputs are forced to the high-impedance state. Thus, data may be latched even when the outputs are not enabled.

The HCT573A is identical in function to the HCT373A but has the Data Inputs on the opposite side of the package from the outputs to facilitate PC board layout.

### **Features**

- Output Drive Capability: 15 LSTTL Loads
- TTL/NMOS-Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 10 μA
- In Compliance with the Requirements Defined by JEDEC Standard No. 7 A
- Chip Complexity: 234 FETs or 58.5 Equivalent Gates
  - Improved Propagation Delays
  - ◆ 50% Lower Quiescent Power
- These Devices are Pb-Free and are RoHS Compliant

## LOGIC DIAGRAM





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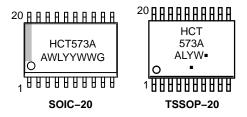


SOIC-20 DW SUFFIX CASE 751D TSSOP-20 DT SUFFIX CASE 948E

## **PIN ASSIGNMENT**

OUTPUT			_
ENABLE C	1 ●	20	□ V <sub>CC</sub>
D0 🗆	2	19	□ Q0
D1 🗆	3	18	⊒ Q1
D2 🗆	4	17	🗆 Q2
D3 🗆	5	16	□ Q3
D4 🗆	6	15	□ Q4
D5 🗆	7	14	□ Q5
D6 🗆	8	13	⊒ Q6
D7 C	9	12	⊒ Q7
GND [	10	11	LATCH
'			ENABLE

## **MARKING DIAGRAMS**



A = Assembly Location

WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G or = Pb-Free Package

(Note: Microdot may be in either location)

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
MC74HCT573ADWR2G	SOIC-20 (Pb-Free)	1000 / Tape & Reel
MC74HCT573ADTR2G	TSSOP-20 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

## **FUNCTION TABLE**

	Output		
Output Enable	Latch Enable	D	Q
L	Н	Н	Н
L	Н	L	L
L	L	Х	No Change
Н	X	Х	Z

X = Don't CareZ = High Impedance

Design Criteria	Value	Units
Internal Gate Count*	58.5	ea
Internal Gate Propagation Delay	1.5	ns
Internal Gate Power Dissipation	5.0	μW
Speed Power Product	0.0075	рЈ

<sup>\*</sup>Equivalent to a two-input NAND gate.

## **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	-0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	$-0.5$ to $V_{CC}$ + 0.5	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	$-0.5$ to $V_{CC} + 0.5$	V
I <sub>in</sub>	DC Input Current, per Pin	±20	mA
l <sub>out</sub>	DC Output Current, per Pin	±25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	±50	mA
P <sub>D</sub>	Power Dissipation in Still Air SOIC Package† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (TSSOP or SOIC Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

†Derating: SOIC Package: -7 mW/°C from 65° to 125°C TSSOP Package: -6.1 mW/°C from 65° to 125°C

## **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter		Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	4.5	5.5	V
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature, All Package Types	<b>-</b> 55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Figure 1)	0	500	ns

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	imit	
Symbol	Parameter	Test Conditions	v <sub>cc</sub> v	–55 to 25°C	≤ <b>85</b> ° <b>C</b>	≤ 125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20  \mu\text{A}$	4.5 5.5	2.0 2.0	2.0 2.0	2.0 2.0	V
V <sub>IL</sub>	Maximum Low–Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20  \mu\text{A}$	4.5 5.5	0.8 0.8	0.8 0.8	0.8 0.8	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 20  \mu\text{A}$	4.5 5.5	4.4 5.4	4.4 5.4	4.4 5.4	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 6.0 \text{ mA}$	4.5	3.98	3.84	3.7	
V <sub>OL</sub>	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 20 \ \mu\text{A}$	4.5 5.5	0.1 0.1	0.1 0.1	0.1 0.1	V
		$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 6.0 \text{ mA}$	4.5	0.26	0.33	0.4	
I <sub>in</sub>	Maximum Input Leakage Current	$V_{in} = V_{CC}$ or GND	5.5	±0.1	±1.0	±1.0	μΑ
I <sub>OZ</sub>	Maximum Three–State Leakage Current	Output in High-Impedance State $V_{in} = V_{IL}$ or $V_{IH}$ $V_{out} = V_{CC}$ or GND	5.5	±0.5	±5.0	±10	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} \le 0 \mu A$	5.5	4.0	40	160	μΑ
$\Delta I_{CC}$	Additional Quiescent Supply Current	V <sub>in</sub> = 2.4 V, Any One Input V <sub>in</sub> = V <sub>CC</sub> or GND, Other Inputs		≥ <b>–</b> 55°C	25°C to	125°C	
	Guirent	$I_{\text{out}} = 0  \mu\text{A}$	5.5	2.9	2	.4	mA

## AC ELECTRICAL CHARACTERISTICS (V<sub>CC</sub> = 5.0 V $\pm 10\%$ , C<sub>L</sub> = 50 pF, Input t<sub>r</sub> = t<sub>f</sub> = 6.0 ns)

		Gı	Guaranteed Limit			
Symbol	Parameter	–55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input D to Output Q (Figures 1 and 5)	30	38	45	ns	
t <sub>PLH</sub> t <sub>PHL</sub>	Maximum Propagation Delay, Latch Enable to Q (Figures 2 and 5)	30	38	45	ns	
T <sub>PLZ,</sub> T <sub>PHZ</sub>	Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6)	28	35	42	ns	
t <sub>TZL,</sub> t <sub>TZH</sub>	Maximum Propagation Delay, Output Enable to Q (Figures 3 and 6)	28	35	42	ns	
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, any Output (Figures 1 and 5)	12	15	18	ns	
C <sub>in</sub>	Maximum Input Capacitance	10	10	10	pF	
$C_{out}$	Maximum Three–State Output Capacitance (Output in High–Impedance State)	15	15	15	pF	

		Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
$C_{PD}$	Power Dissipation Capacitance (Per Enabled Output)*	48	pF

<sup>\*</sup> Used to determine the no–load dynamic power consumption:  $P_D = C_{PD} \ V_{CC}^2 f + I_{CC} \ V_{CC}$ .

## **TIMING REQUIREMENTS** (V<sub>CC</sub> = 5.0 V $\pm$ 10%, C<sub>L</sub> = 50 pF, Input t<sub>r</sub> = t<sub>f</sub> = 6.0 ns)

			Guaranteed Limit						
			–55 to	25°C	≤ 85	5°C	≤ 12	5°C	
Symbol	Parameter	Fig.	Min	Max	Min	Max	Min	Max	Unit
t <sub>su</sub>	Minimum Setup Time, Input D to Latch Enable	4	10		13		15		ns
t <sub>h</sub>	Minimum Hold Time, Latch Enable to Input D	4	5.0		5.0		5.0		ns
t <sub>w</sub>	Minimum Pulse Width, Latch Enable	2	15		19		22		ns
t <sub>r</sub> , t <sub>f</sub>	Maximum Input Rise and Fall Times	1		500		500		500	ns

## **SWITCHING WAVEFORMS**

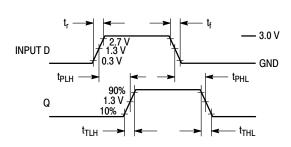


Figure 1.

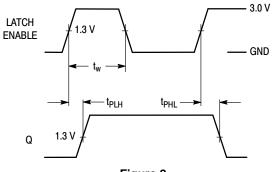


Figure 2.

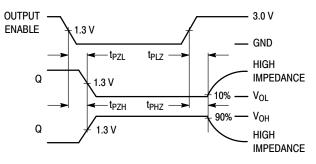


Figure 3.

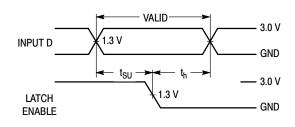
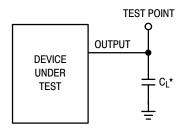


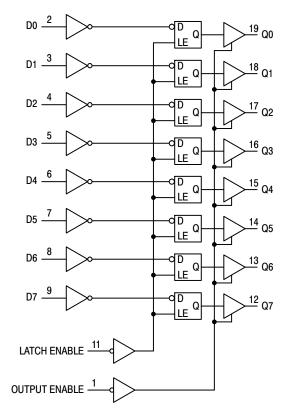
Figure 4.

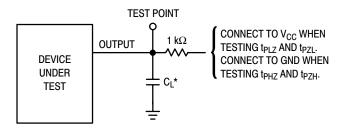
**EXPANDED LOGIC DIAGRAM** 



\*Includes all probe and jig capacitance

Figure 5. Test Circuit



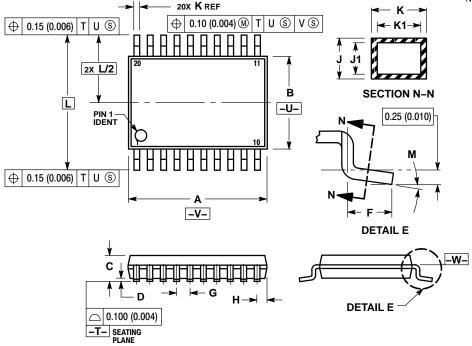


\*Includes all probe and jig capacitance

Figure 6. Test Circuit

### PACKAGE DIMENSIONS

## TSSOP-20 **DT SUFFIX** CASE 948E-02 **ISSUE C**



- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION:
  MILLIMETER.
  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
  5. DIMENSION K DOES NOT INCLUDE

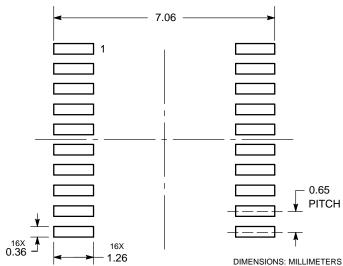
  - SHALL NOT EACEED 0.25 (0.010) FER S
    5. DIMENSION K DOES NOT INCLUDE
    DAMBAR PROTRUSION. ALLOWABLE
    DAMBAR PROTRUSION SHALL BE 0.08
    (0.003) TOTAL IN EXCESS OF THE K
    DIMENSION AT MAXIMUM MATERIAL
    CONDITION.
  - CONDITION.

    6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

    7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	BSC	
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252 BSC		
M	0°	8°	0°	8°	

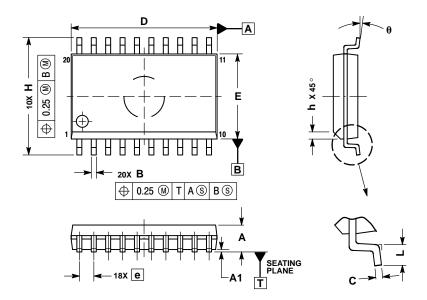
## **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## PACKAGE DIMENSIONS

SOIC-20 DW SUFFIX CASE 751D-05 ISSUE G



#### NOTES:

- DIMENSIONS ARE IN MILLIMETERS.
- INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
- 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- MAXIMUM MOLD PROTROSION 1.15 PEA 318
   DIMENSION B DOES NOT INCLUDE DAMBAR
   PROTRUSION. ALLOWABLE PROTRUSION
   SHALL BE 0.13 TOTAL IN EXCESS OF B
   DIMENSION AT MAXIMUM MATERIAL
   CONDITION.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
В	0.35	0.49		
С	0.23	0.32		
D	12.65	12.95		
E	7.40	7.60		
е	1.27	BSC		
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
θ	0°	7 °		

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